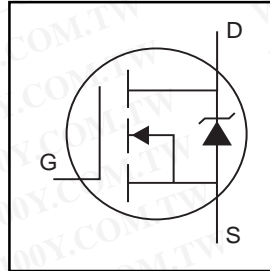


- Advanced Process Technology
- Optimized for 4.5V-7.0V Gate Drive
- Ideal for CPU Core DC-DC Converters
- Fast Switching

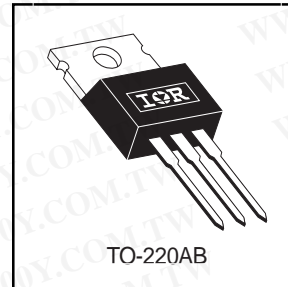
### Description

These HEXFET Power MOSFETs were designed specifically to meet the demands of CPU core DC-DC converters in the PC environment. Advanced processing techniques combined with an optimized gate oxide design results in a die sized specifically to offer maximum efficiency at minimum cost.

The TO-220 package is universally preferred for all commercial-industrial applications at power dissipation levels to approximately 50 watts. The low thermal resistance and low package cost of the TO-220 contribute to its wide acceptance throughout the industry.



$V_{DSS} = 20V$
$R_{DS(on)} = 0.016W$
$I_D = 48A$



### Absolute Maximum Ratings

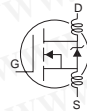
	Parameter	Max.	Units
$I_D @ T_C = 25^\circ C$	Continuous Drain Current, $V_{GS} @ 4.5V$	48	A
$I_D @ T_C = 100^\circ C$	Continuous Drain Current, $V_{GS} @ 4.5V$	30	
$I_{DM}$	Pulsed Drain Current ①	190	
$P_D @ T_C = 25^\circ C$	Power Dissipation	69	W
	Linear Derating Factor	0.56	W/°C
$V_{GS}$	Gate-to-Source Voltage	$\pm 10$	V
$V_{GSM}$	Gate-to-Source Voltage (Start Up Transient, $t_p = 100\mu s$ )	14	V
$E_{AS}$	Single Pulse Avalanche Energy②	270	mJ
$I_{AR}$	Avalanche Current①	29	A
$E_{AR}$	Repetitive Avalanche Energy①	6.9	mJ
$dv/dt$	Peak Diode Recovery $dv/dt$ ③	5.0	V/ns
$T_J$	Operating Junction and	-55 to + 150	°C
$T_{STG}$	Storage Temperature Range		
	Soldering Temperature, for 10 seconds		
	Mounting torque, 6-32 or M3 screw	300 (1.6mm from case ) 10 lbf•in (1.1N•m)	

### Thermal Resistance

	Parameter	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case	—	1.8	°C/W
$R_{\theta CS}$	Case-to-Sink, Flat, Greased Surface	0.50	—	
$R_{\theta JA}$	Junction-to-Ambient	—	62	

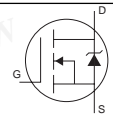
## Electrical Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	20	—	—	V	$V_{GS} = 0V, I_D = 250\mu A$
$dV_{(BR)DSS}/dT_J$	Breakdown Voltage Temp. Coefficient	—	0.029	—	V/ $^\circ\text{C}$	Reference to $25^\circ\text{C}, I_D = 1\text{mA}$
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	—	—	0.019	m	$V_{GS} = 4.5V, I_D = 29A$ ④
		—	—	0.016		$V_{GS} = 7.0V, I_D = 29A$ ④
$V_{GS(th)}$	Gate Threshold Voltage	0.70	—	—	V	$V_{DS} = V_{GS}, I_D = 250\mu A$
$g_{fs}$	Forward Transconductance	28	—	—	S	$V_{DS} = 16V, I_D = 29A$
$I_{DSS}$	Drain-to-Source Leakage Current	—	—	25	$\mu A$	$V_{DS} = 20V, V_{GS} = 0V$
		—	—	250		$V_{DS} = 10V, V_{GS} = 0V, T_J = 150^\circ\text{C}$
$I_{GSS}$	Gate-to-Source Forward Leakage	—	—	100	nA	$V_{GS} = 10V$
	Gate-to-Source Reverse Leakage	—	—	-100		$V_{GS} = -10V$
$Q_g$	Total Gate Charge	—	—	43	nC	$I_D = 29A$
$Q_{gs}$	Gate-to-Source Charge	—	—	12		$V_{DS} = 16V$
$Q_{gd}$	Gate-to-Drain ("Miller") Charge	—	—	13		$V_{GS} = 4.5V$ , See Fig. 6 ④
$t_{d(on)}$	Turn-On Delay Time	—	9.8	—		$V_{DD} = 10V$
$t_r$	Rise Time	—	100	—	ns	$I_D = 29A$
$t_{d(off)}$	Turn-Off Delay Time	—	63	—		$R_G = 9.5\Omega, V_{GS} = 4.5V$
$t_f$	Fall Time	—	82	—		$R_D = 0.3\Omega$ , ④
$L_D$	Internal Drain Inductance	—	4.5	—	nH	Between lead, 6mm (0.25in.) from package and center of die contact
$L_S$	Internal Source Inductance	—	7.5	—		
$C_{iss}$	Input Capacitance	—	2000	—	pF	$V_{GS} = 0V$
$C_{oss}$	Output Capacitance	—	800	—		$V_{DS} = 15V$
$C_{rss}$	Reverse Transfer Capacitance	—	290	—		$f = 1.0\text{MHz}$ , See Fig. 5



## Source-Drain Ratings and Characteristics

	Parameter	Min.	Typ.	Max.	Units	Conditions
$I_S$	Continuous Source Current (Body Diode)	—	—	48	A	MOSFET symbol showing the integral reverse p-n junction diode.
$I_{SM}$	Pulsed Source Current (Body Diode) ①	—	—	190		
$V_{SD}$	Diode Forward Voltage	—	—	1.3	V	$T_J = 25^\circ\text{C}, I_S = 29A, V_{GS} = 0V$ ④
$t_{rr}$	Reverse Recovery Time	—	68	100	ns	$T_J = 25^\circ\text{C}, I_F = 29A$
$Q_{rr}$	Reverse Recovery Charge	—	130	190	nC	$di/dt = 100A/\mu s$ ④
$t_{on}$	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by $L_S+L_D$ )				



### Notes:

- ① Repetitive rating; pulse width limited by max. junction temperature.
- ② Starting  $T_J = 25^\circ\text{C}$ ,  $L = 0.64\text{mH}$   
 $R_G = 25\Omega, I_{AS} = 29A$ .
- ③  $I_{FD} \leq 29A, di/dt \leq 63A/\mu s, V_{DD} \leq V_{(BR)DSS}, T_J \leq 150^\circ\text{C}$
- ④ Pulse width  $\leq 300\mu s$ ; duty cycle  $\leq 2\%$ .

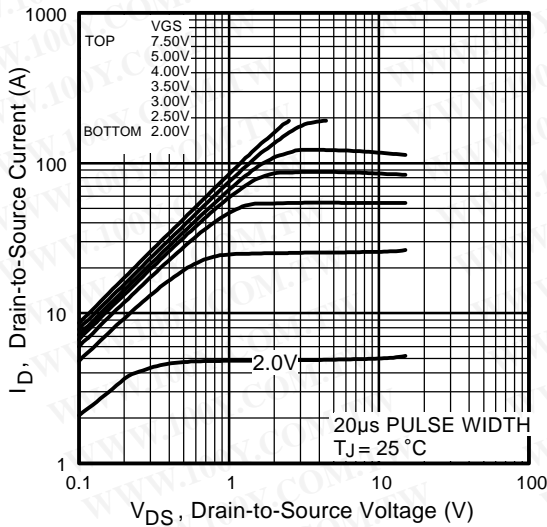


Fig 1. Typical Output Characteristics

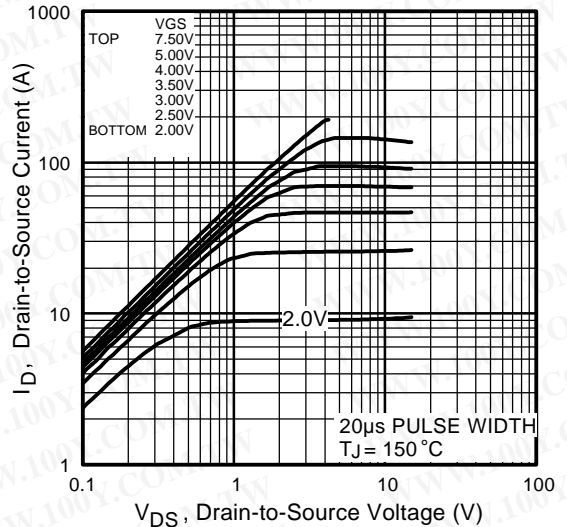


Fig 2. Typical Output Characteristics

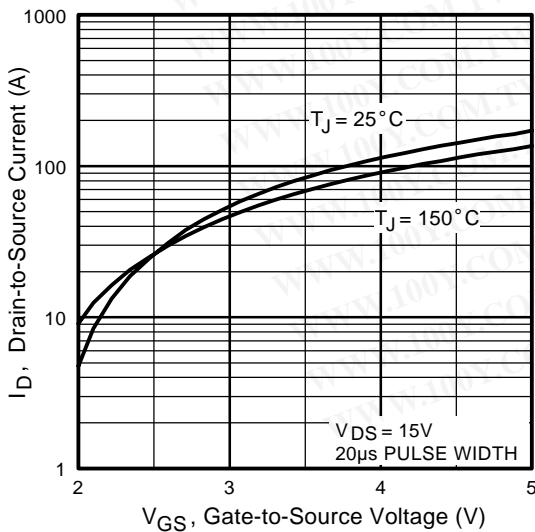


Fig 3. Typical Transfer Characteristics

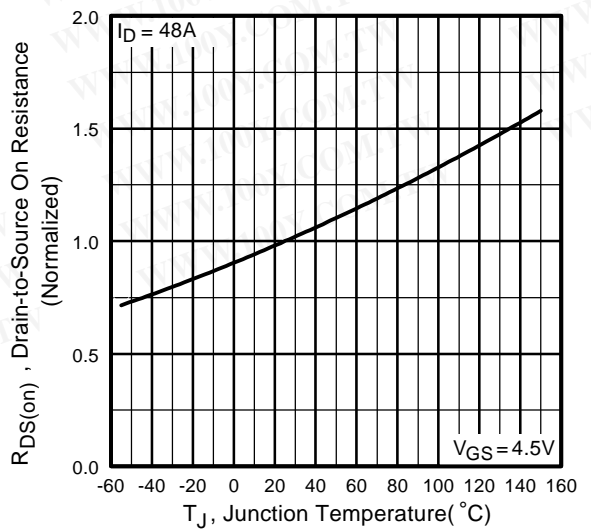
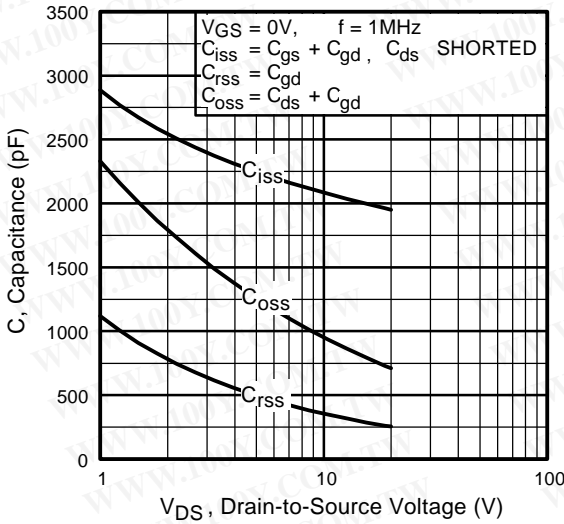


Fig 4. Normalized On-Resistance Vs. Temperature

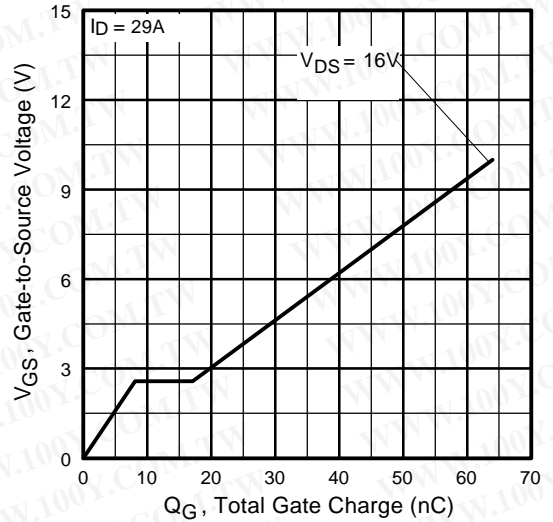
# IRL3202

勝特力材料 886-3-5753170  
 勝特力电子(上海) 86-21-54151736  
 勝特力电子(深圳) 86-755-83298787  
[Http://www.100y.com.tw](http://www.100y.com.tw)

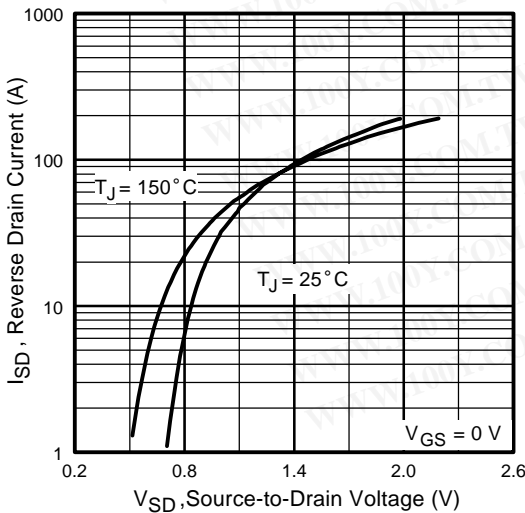
International  
**IR** Rectifier



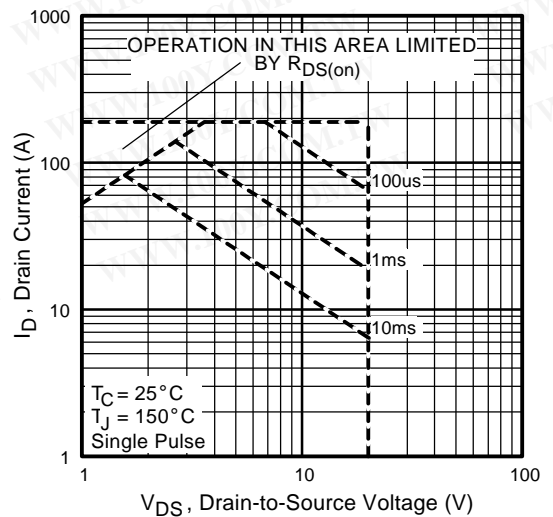
**Fig 5.** Typical Capacitance Vs. Drain-to-Source Voltage



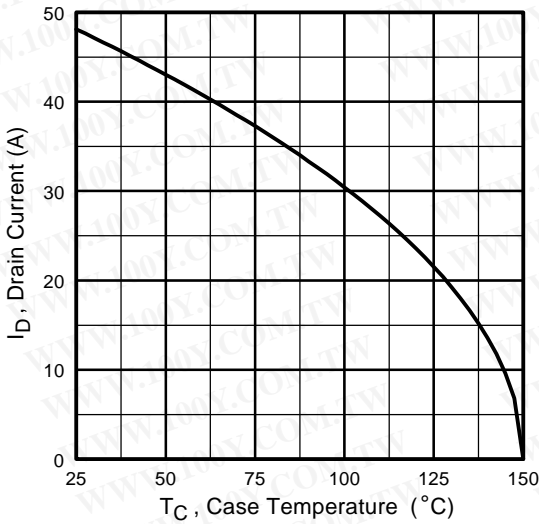
**Fig 6.** Typical Gate Charge Vs. Gate-to-Source Voltage



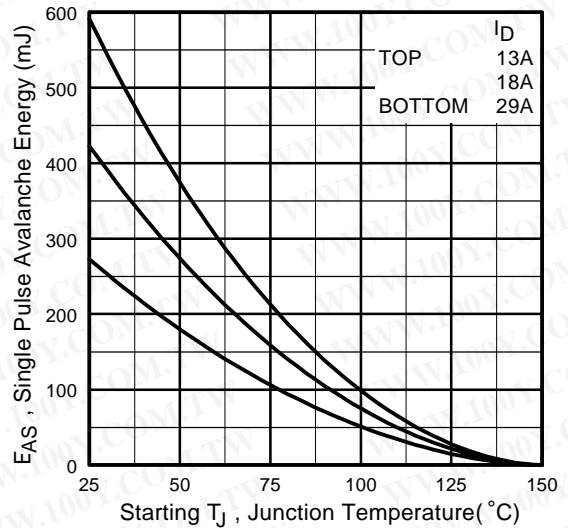
**Fig 7.** Typical Source-Drain Diode Forward Voltage



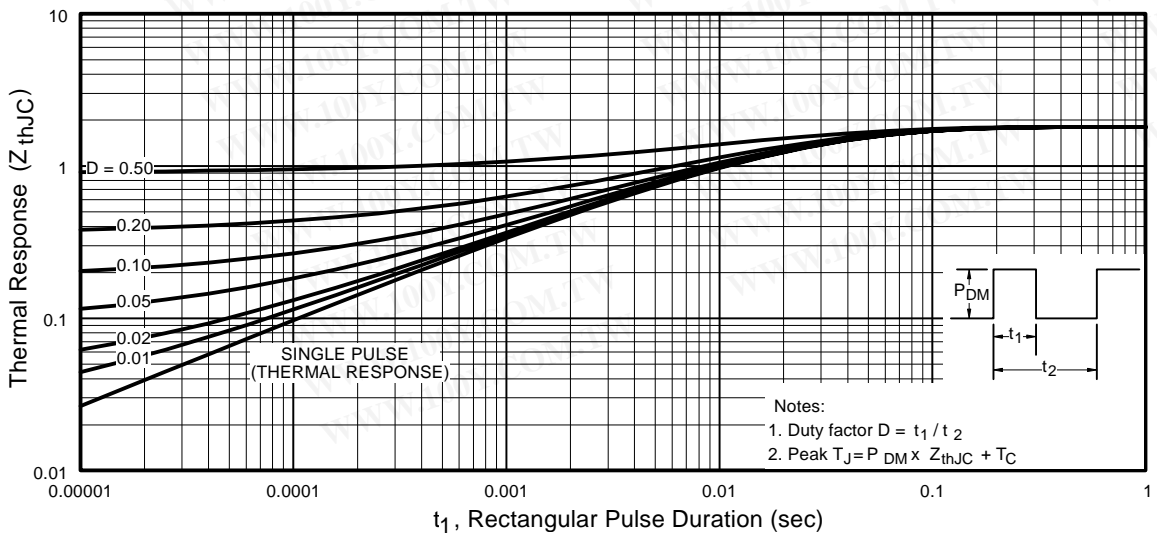
**Fig 8.** Maximum Safe Operating Area



**Fig 9.** Maximum Drain Current Vs. Case Temperature



**Fig 10.** Maximum Avalanche Energy Vs. Drain Current



**Fig 11.** Maximum Effective Transient Thermal Impedance, Junction-to-Case

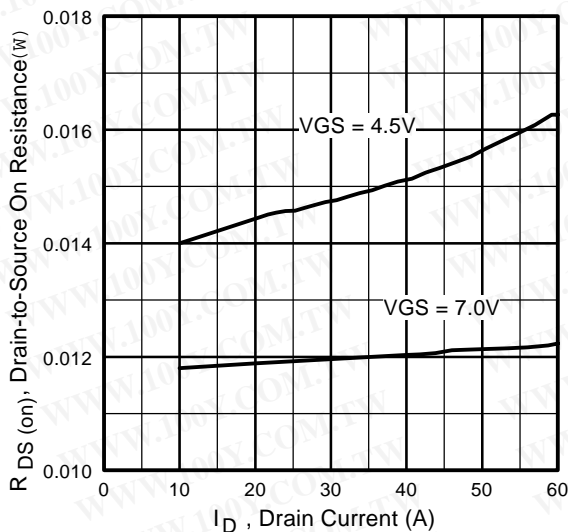


Fig 12. On-Resistance Vs. Drain Current

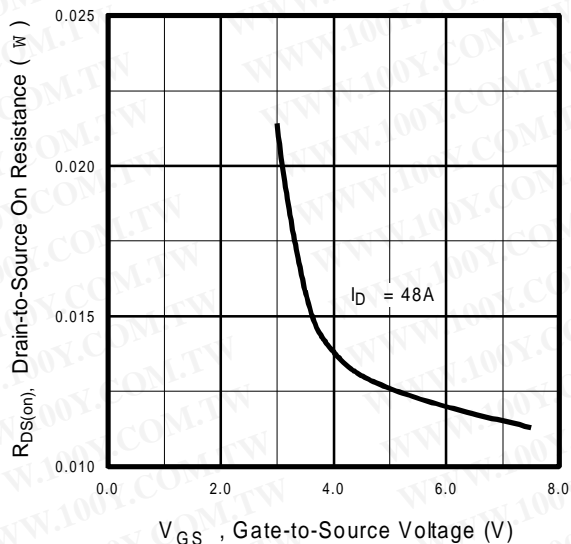
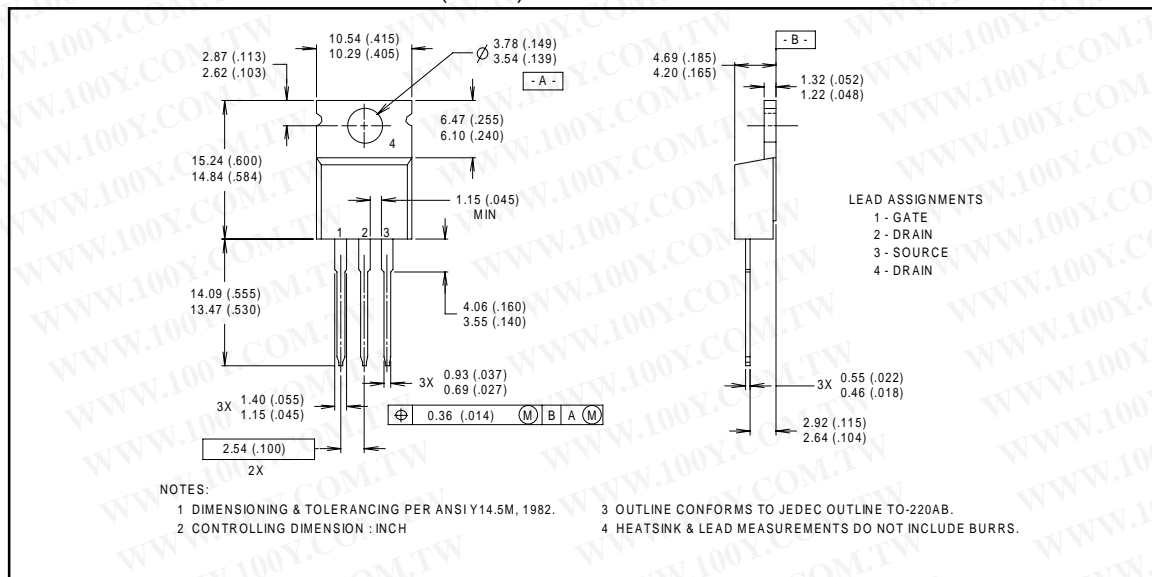


Fig 13. On-Resistance Vs. Gate Voltage

## Package Outline

### TO-220AB Outline

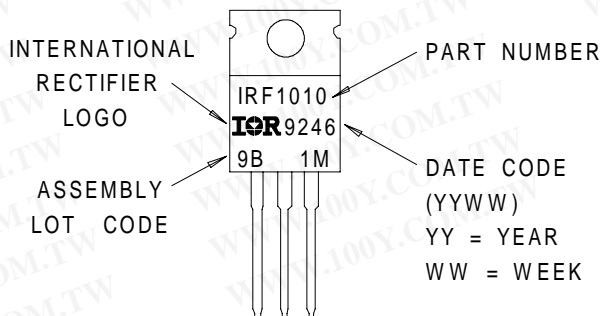
Dimensions are shown in millimeters (inches)



## Part Marking Information

### TO-220AB

EXAMPLE : THIS IS AN IRF1010  
 WITH ASSEMBLY  
 LOT CODE 9B1M



International  
**IR** Rectifier

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**EUROPEAN HEADQUARTERS:** Hurst Green, Oxted, Surrey RH8 9BB, UK Tel: ++ 44 1883 732020

**IR CANADA:** 7321 Victoria Park Ave., Suite 201, Markham, Ontario L3R 2Z8, Tel: (905) 475 1897

**IR GERMANY:** Saalburgstrasse 157, 61350 Bad Homburg Tel: ++ 49 6172 96590

**IR ITALY:** Via Liguria 49, 10071 Borgaro, Torino Tel: ++ 39 11 451 0111

**IR FAR EAST:** K&H Bldg., 2F, 30-4 Nishi-Ikebukuro 3-Chome, Toshima-Ku, Tokyo Japan 171 Tel: 81 3 3983 0086

**IR SOUTHEAST ASIA:** 315 Outram Road, #10-02 Tan Boon Liat Building, Singapore 0316 Tel: 65 221 8371

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